- A first-order reaction A→P, with forward reaction rate, k<sub>1,s</sub>, takes place inside a spherical catalyst. The catalyst is 6x10<sup>-3</sup> m in diameter and has a surface area per unit volume, a, of 2x10<sup>8</sup> m<sup>2</sup>/m<sup>3</sup> catalyst.
  - (a) Obtain an expression for the concentration profile of A inside the catalyst, and
  - (b) Determine the value of the effectiveness,  $\eta$

Provided data/equations: Effective diffusivity  $D_{Ae} = 1.26 \times 10^{-4} \text{ m}^2/\text{h}$ 

Surface reaction rate constant:  $k_{1s} = 1.728 \times 10^{-7} \text{ m}^3/\text{h} \text{ m}^2$ 

Concentration of A at catalyst surface  $C_{A,S} = 28 \text{ kgmol/m}^3$ 

From handout on Example 3.2-8:

$$C_A = C_{A,S} \frac{R}{r} \frac{\sinh\left(\frac{3\phi r}{R}\right)}{\sinh(3\phi)}$$
$$\eta = \frac{1}{3\phi} (3\phi \coth(3\phi) - 1)$$

- 2. 3-3 Oxygen Diffusion in Tissues. Oxygen is consumed in the body tissue, or by cells maintained in vitro, at a rate which is often nearly independent of the O<sub>2</sub> concentration. As a model for a tissue region or aggregate of cells, consider steady-state O<sub>2</sub> diffusion in a sphere of radius, r<sub>o</sub>, with zero-order consumption of O<sub>2</sub>. Assume that the O<sub>2</sub> concentration at the outer surface (r=r<sub>o</sub>) is maintained constant at C<sub>o</sub>. Determine the O<sub>2</sub> concentration profile, C(r).
- 3. 3-11 Peltier Effect. When a melt is an electrical conductor and its solid is a semiconductor, passing a current from the solid to the melt releases heat at the interface, a phenomenon called the Peltier effect. As shown in the figure, suppose that layers of molten and solid silicon are confined between graphite plates separated by a distance L. Both phases occur because the melting temperature of silicon ( $T_m$ ) is between the temperature of the plates (i.e.,  $T_1 < T_m < T_2$ ). Assume that temperature variations in the x and y directions can be neglected and that the system is at steady state.
  - a. If there is no electrical current, calculate T(z) in both silicon phases and find the height, h, of the melt-solid interface. The thermal conductivities of the melt and solid are  $k_m$  and  $k_s$ ,  $k_m \neq k_s$ . The heat of fusion is  $\lambda$ .
  - b. With an electrical current present, the rate of energy release at the interface is given by  $H_s = \beta \times i_z$ , where  $\beta$  is the Peltier coefficient (volts) and  $i_z$  is the current density in the z direction (A/m<sup>2</sup>). Determine T(z) and h.



Solution to HW3

Chem F 530

1) (a) Determine CA(r) inside the catalyst assume homogeneous reaction within catelyst from lecture:  $C_{A} = C_{AS} \frac{R}{\Gamma} \frac{\sinh(3\phi T_{R})}{\sinh(3\phi)}$  $\phi = \frac{V_P}{S_r} \sqrt{\frac{\alpha k_{1S}}{D_A}}$ K,V = 9 CAS = 28 hsmol/m3  $R = 3 \times 10^{-3} m$  $\frac{V_{f}}{S_{x}} = \frac{4}{3} \frac{\pi R^{3}}{4 \pi R^{2}} = 10^{-3} m$ a = 2 × 10 8 m²/m² cat  $k_{1S} = \frac{k_{1V}}{a} = 1.728 \times 10^{-7} \frac{1}{\ln(\frac{m^2}{m^3 \cos t})}$ DAe = 1.26 × 10-4 m2/h (h... hour) Plug the values into equations  $\implies \phi = 0.5237$  $\implies C_A = 0.0365 \operatorname{sub}(523.7r)$ 

CLIEME 530 cont. Problem 1 Solution to HW3 (b) Determine the effectiveness factor decture:  $\gamma = \frac{1}{3\phi^2} (3\phi \coth 3\phi - 1)$  $\phi = 05237$  from (a) => 2 = 0,867 this is close to unity; i.e., most of the scialyst volume is reacting at high rate (reactant is able to diffune

quickly)

WMD 3-3. Oxygenation of Cell Aggregates r = radius of anoxic core (if present) Ry = {-ko, c>0 cells----くさつ (a) Determine (Cr) (>0 throughout sphere Case 1  $0 = \frac{D}{r^2} \frac{d}{dr} \left( \frac{r^2 dC}{dr} \right) - k_0$ Table 2- $\frac{1}{r^2} \frac{d}{dr} \left( \frac{r^2 dC}{dr} \right) = \frac{k_0}{D}$  $\frac{dc}{dc}(o) = 0 \quad c(r_{0}) = c_{0}$ Integrate DE directly and apply BCIs: O from symmetry BC  $r^{2} \frac{dc}{dr} = \frac{k_{0} r^{3}}{D} + \alpha^{7}$  $c(r) = \frac{k_0}{D} \frac{r^2}{\xi} + b$  $C(r_{5}) = C_{0} = \frac{k_{0}}{D} \frac{r_{0}^{2}}{6} + b \Rightarrow b = C_{0} - \frac{k_{0}r_{0}^{2}}{6D}$  $C(r) = C_0 - \frac{k_0 r_0^2}{6D} \left[ 1 - \left(\frac{r}{r_0}\right)^2 \right]$ The minimum O2 concentration is at Y=0,  $C(o) = C_0 - \frac{k_0 r_0^2}{6D}$ 

1/22/11

## 3-11, Peltier Effect

(a) Temperature and interface location without current dzt = 0 in both phoses => T(z) linear in each  $T(2) = \begin{cases} a_1 + a_2 2 & \text{in solid}, & 0 \le 2 \le h \\ b_1 + b_2 2 & \text{in melt}, & h \le 2 \le L \end{cases}$ To be determined : a, b, a, b, h. Conditions: (1) bottom temp  $T(0) = T_1$ (2) top temp.  $T(L) = T_2$  $T(h^{-}) = T(h^{+}) = T_{m}$  (3),(4) meiting temp.  $k_s \frac{dT}{dz}(h^-) = k_m \frac{dT}{dz}(h^+)$  (5) 92 continuous at interface [qz is continuous at z=h because there is no flow, no interfacial motion, and no interfacial energy input. See Eq. (2.5-12).] Using (1) and (3), the solid temp. is  $T(z) = T_1 + (T_m - T_1) = 0 \le z \le h$ Using (2) and (4), the melt temp. is  $T(2) = T_2 + (T_m - T_2)(L-2)$   $h \le 2 \le L$ Applying (5) determines h (see next page).

	$k_{s} \underbrace{(T_{m}-T_{1})}_{h} = k_{m} \underbrace{(T_{2}-T_{m})}_{L-h}$
· · · · · · · · · · · · · · · · · · ·	$h\left[k_{s}\left(T_{m}-T_{i}\right)+k_{m}\left(T_{2}-T_{m}\right)\right]=k_{s}L\left(T_{m}-T_{i}\right)$
· · · · · · · · · · · · · · · · · · · ·	$h = k_{s}L(T_{m}-T_{i})$ $k_{s}(T_{m}-T_{i}) + k_{m}(T_{2}-T_{m})$
· · ·	
· · · · · · · · · · · · · · · · · · ·	$\frac{b}{L} = \frac{1}{1 + km(T_2 - T_m)}$
	$\left[ \frac{k_{s}(T_{m}-T_{l})}{k_{s}(T_{m}-T_{l})} \right]$
(ح)	Temperature and interface location with current
· · · · · · ·	Same formulation, except (5) must be modified to include heat generation at interface:
	$q_2(h^+) - q_2(h^-) = H_s$ (5')
	T(2) in both phases is unchanged, except for h. Applying (5'),
	$\frac{-k_m(T_2-T_m)}{L-h} + \frac{k_s(T_m-T_l)}{h} = H_s$
· · · · · · · · · · · · · · · · · · · ·	$-k_mh(T_2-T_m)+k_s(L-h)(T_m-T_1)=H_sh(L-h)$
	$H_{sh^{2}} - \left[k_{s}(T_{m}-T_{i}) + k_{m}(T_{2}-T_{m}) + H_{sL}\right]h$
· · · · · · · · · · · · · · · · · · ·	$+ k_{s}L(T_{m}-T_{i}) = 0$
· · · · · · · ·	
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This is a quadratic :  $H_sh^2 + bh + C = 0$  $b = -\left[k_{s}(T_{m}-T_{i}) + k_{m}(T_{2}-T_{m}) + H_{s}L\right]$  $C = k_{SL}(T_m - T_i)$  $\frac{h}{L} = \frac{-b \pm \sqrt{b^2 - 4H_sc}}{2H_sL}$ The correct root is the one which reduces to the result in (a) for 1+5 > 0. From (a),  $\frac{h}{L} = \frac{1}{1+A} \qquad A \equiv \frac{h}{h} \left( \frac{T_2 - T_m}{T_2 - T_1} \right)$ For comparison, rearrange the quadratic solution :  $b = -\frac{c}{L}(I + A + H) \quad H = \frac{H_s L^2}{c}$  $\frac{h}{L} = \frac{1+A+H}{2} \pm \sqrt{(1+A+H)^2 - 4H}$ The numerator (N) and denominator (D) of hill both = 0 at 14=0, so use L'Hopital's rule to find limit :  $\frac{1}{100} = \frac{dN/dH}{dD/dH} = \frac{1}{2} \frac{dN}{dH}$  $\frac{dN}{dH} = 1 \pm \frac{1}{2} \left[ (1 + A + 1H)^2 - 4H \right]^{-1/2} \left[ 2 (1 + A + H) - 4 \right]$  $\frac{dN}{dH}\Big|_{H=0} = 1 \pm \frac{1}{2(1+A)} \left[ 2(1+A) - 4 \right] = 1 \pm \left(1 - \frac{2}{1+A}\right)$ 

$\frac{dN}{dH} = \frac{(A+1) \pm (A-1)}{A+1}$	
CHINO AT	· · · · · · · · · · · · · · · · · · ·
$\lim_{\substack{h \to 0}} \frac{h}{L} = (A+I) \pm (A-I)$	
	······
$= \int \frac{A}{A+1}  \text{for "+" root}$	
1 for "-" root A+1	
of The "-" root is correct and	
$h = 1 + A + H - \sqrt{(1 + A + H)^2 - 4H}$	(A and H defined
L 2H	On P.3)
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